

ABSTRACT

A semiconductor storage device has a memory string including a memory cell, a bit line electrically connected to one end of the memory string, and a sense amplifier electrically connected to the bit line. The sense amplifier has a first transistor, one end of which is connected to a first node on an electric current path of the bit line, and another end of which is electrically connected to a second node, a second transistor electrically connected between the second node and a sense node, and a third transistor, a gate of which is connected to the first node, and the third transistor being electrically connected between the second node and a third node whose voltage can be adjusted.